

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend the paragraph starting at page 4, line 11, as follows:

On the Al component-free buffer layer 3 is formed a multilayer structure 4 that is a multilayer block of thin-film layers of compositions represented by the general formula $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x < 1$). In this embodiment, the multilayer structure 4 is formed by conducting MOCVD to successively epitaxially grow on the buffer layer 3 an $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ layer 41, and $\text{Al}_{0.15}\text{Ga}_{0.85}\text{As}$ layer 42 and an ~~$\text{Al}_{0.6}\text{Ga}_{0.4}\text{As}$ layer 43~~ $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ layer 43 on the buffer layer 3, each to a thickness several times greater than the 100 nm thickness of the buffer layer 3. Specifically, the $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ layer 41 is formed to a thickness of 500 nm, the $\text{Al}_{0.15}\text{Ga}_{0.85}\text{As}$ layer 42 to a thickness of 1000 nm and the ~~$\text{Al}_{0.6}\text{Ga}_{0.4}\text{As}$ layer 43~~ $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ layer 43 to a thickness of 500 nm.